

Patent Abstracts of Japan

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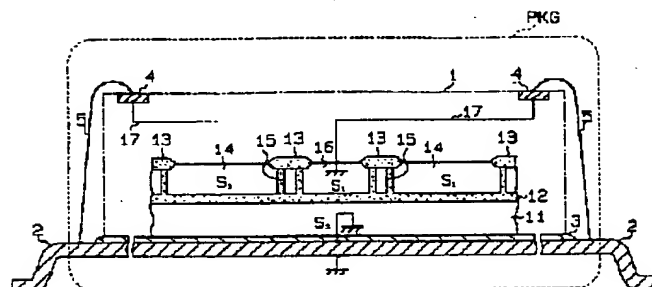
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 APPLICATION NUMBER : 06129324

APPLICANT : NIPPONDENSO CO LTD;

INVENTOR : FUJINO SEIJI;

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TITLE : SEMICONDUCTOR DEVICE



ABSTRACT : PURPOSE: To improve heat radiation efficiency of a semiconductor device which incorporates a semiconductor chip having an SOI(Silicon On Insulator) structure without increasing a package size and cost.

CONSTITUTION: A semiconductor chip 1 having an SOI structure is bonded to a die pad 2 in the state where the back surface of a semiconductor substrate 11 of the semiconductor chip 1 is set to reference potential and electric conduction is kept between the back surface of the semiconductor substrate 11 and the lead frame (die pad) 2. In contrast, there is provided a heat dissipation pad 4 on the surface of the semiconductor chip 1 where electric conduction is kept with a part (buffer region 16) set to reference potential on an insulating film 12 inside the surface. The heat radiation pad 4 and the lead frame (external connection lead part) 2 are electrically connected with each other through a heat radiation lead wire 5, and hence heat produced on the insulating film 12 is dissipated on the lead frame 2 through the heat radiation pad 4 and the heat radiation lead wire 5.

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